

# Structural interpretation of the vibrational spectra of fa-

Physical Review B

19, 2064-2073

DOI: [10.1103/physrevb.19.2064](https://doi.org/10.1103/physrevb.19.2064)

Citation Report

#	ARTICLE	IF	CITATIONS
1	Transport and recombination in hydrogenated amorphous silicon. , 1984, , 133-161.		3
2	Short-range order in amorphous semiconductors. Topics in Applied Physics, 1979, , 215-250.	0.4	34
3	Photoemission studies on <i>in situ</i> prepared hydrogenated amorphous silicon films. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1979, 40, 433-450.	0.6	127
4	Microstructure of plasma-deposited $\text{Si:H}$ films. Applied Physics Letters, 1979, 35, 244-246.	1.5	291
5	Optical properties and hydrogen concentration in amorphous silicon. Thin Solid Films, 1979, 62, 327-336.	0.8	76
6	Spectroscopic evidence for valence-alternation-pair defect states in vitreous $\text{SiO}_2$ . The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1979, 39, 513-530.	0.6	167
7	Proton NMR Spin-Lattice Relaxation Time Characterization of a-Si(H) Structure. Materials Research Society Symposia Proceedings, 1980, 3, 341.	0.1	1
8	Studies of the mechanism of the decomposition of hydrogenated a-Si films. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1980, 42, 671-681.	0.6	40
9	Optical properties of hydrogenated sputtered silicon in the 0-13 eV photon energy range. Solar Energy Materials and Solar Cells, 1980, 4, 1-10.	0.4	13
10	Infrared Spectrum and Structure of Hydrogenated Amorphous Silicon. Physica Status Solidi (B): Basic Research, 1980, 100, 43-56.	0.7	500
11	The Acoustic Local Mode of H, D, and F in Amorphous Germanium and Silicon. Physica Status Solidi (B): Basic Research, 1980, 101, 451-459.	0.7	23
12	Structural studies of hydrogenated amorphous silicon. Solar Cells, 1980, 2, 409-419.	0.6	13
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14	Small angle x-ray and neutron scattering studies of plasma-deposited amorphous silicon-hydrogen films. Solid State Communications, 1980, 33, 973-977.	0.9	58
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17	Mass spectrometry of a silane glow discharge during plasma deposition of a-Si: H films. Thin Solid Films, 1980, 67, 309-320.	0.8	140
18	Amorphous semiconducting Si:H. Bulletin of Materials Science, 1980, 2, 295-315.	0.8	1

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20	Emission spectroscopy of SiH in a silane glow-discharge. Journal Physics D: Applied Physics, 1980, 13, 759-765.	1.3	59
21	Proton Magnetic Resonance Spectra of Plasma-Deposited Amorphous Si: H Films. Physical Review Letters, 1980, 44, 193-196.	2.9	227
22	Bonding of fluorine in amorphous hydrogenated silicon. Physical Review B, 1980, 22, 6140-6148.	1.1	101
23	Bombardment-produced disorder and SiH bonds in crystalline and amorphous silicon. Physical Review B, 1980, 22, 6233-6239.	1.1	26
24	Silane dissociation mechanisms and thin film formation in a low pressure multipole dc discharge. Applied Physics Letters, 1980, 37, 646-648.	1.5	83
25	Effect of deposition temperature and annealing on optically detected magnetic resonance in GD a-Si. Journal of Non-Crystalline Solids, 1980, 35-36, 633-638.	1.5	7
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34	Microstructure and properties of rfsputtered amorphous hydrogenated silicon films. Journal of Applied Physics, 1981, 52, 5329-5339.	1.1	120
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133	Chapter 12 Photoelectron Emission Studies. Semiconductors and Semimetals, 1984, , 385-426.	0.4	1
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